Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

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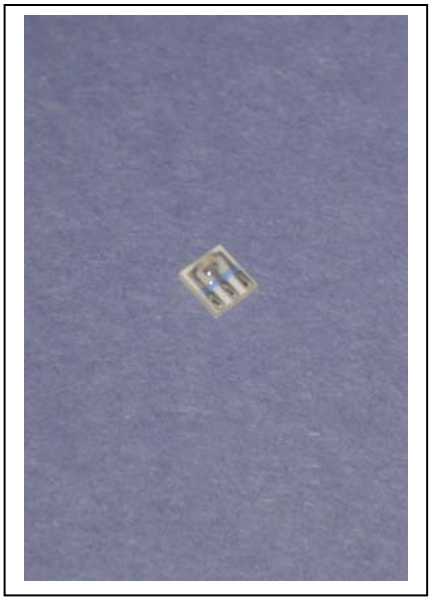
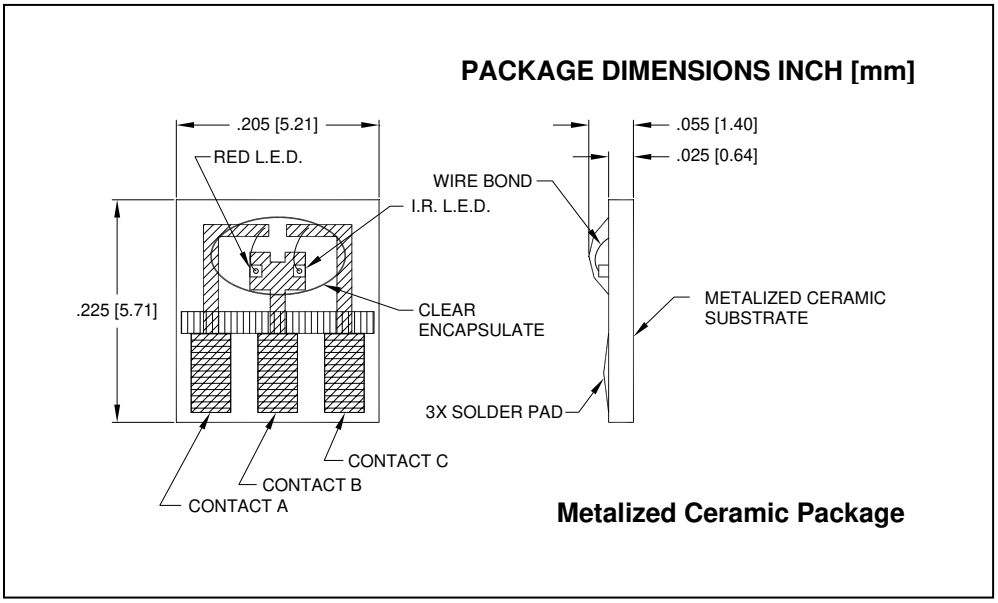
GaAlAs High power IR LED Emitters

(660nm/940nm) PDI-E835





FEATURES

- Low Cost
- 660 nm +/- 3nm
- 3 drive line

DESCRIPTION

The **PDI-E835** is a three drive line dual emitter oximeter component. The 660 and 940nm GaAlAs infrared emitters are mounted in a glob toped low cost ceramic SMT package. The LEDs have a common anode.

APPLICATIONS

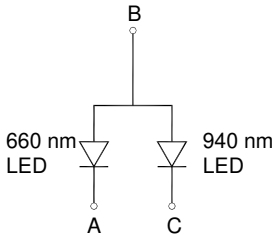
- Oximeter Probes
- Finger Clamps
- Reusable probes

ABSOLUTE MAXIMUM RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	PARAMETER	MIN	MAX	UNITS
P_d	Power Dissipation		250	mW
I_f	Continuous Forward Current		30	mA
I_p	Peak Forward Current		200	mA
V_r	Reverse Voltage		4	V
T_{STG}	Storage Temperature	-40	+80	°C
T_O	Operating Temperature	-40	+80	°C
T_S	Soldering Temperature*		+240	°C

* 1/16 inch from case for 3 seconds max.

SCHEMATIC



ELECTRO-OPTICAL CHARACTERISTICS RATING (TA)= 23°C UNLESS OTHERWISE NOTED

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	660 nm			940 nm			UNITS
			MIN	TYP	MAX	MIN	TYP	MAX	
P_o	Radiant Flux	I_f = 20 mA	1.8	2.4		1.2	2.0		mW
Iv	Luminous Intensity	I_f= 20 mA	20	57					mcd
V_f	Forward Voltage	I_f = 20 mA		1.8	2.4		1.3	1.5	V
V_r	Reverse Breakdown Voltage	I_f = 10 μA	5			5			V
λ_p	Peak Wavelength	I_f = 20 mA	658	661	664	930	940	950	nm
$\Delta\lambda$	Spectral Halfwidth	I_f = 20 mA		22			42		nm
t_r	Rise Time	I_f = 20 mA		0.08			2		uS
t_f	Fall Time	I_f = 20 mA		0.03			1		uS

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